

**JST131N2-600E 1A TRIAC**

Rev.A.1.1

DESCRIPTION:

The JST131N2-600E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Package SOT-89-2L is RoHS compliant.

MAIN FEATURES**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c = 58^\circ\text{C}$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	16.5	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		18	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1.36	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	-	70	$\text{A}/\mu\text{s}$
		40	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W

Peak gate power

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
				25	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	15	mA
				30	
I_H	$I_T=50mA$		MAX.	15	mA
dV/dt	$V_D=400V$ Gate Open $T_j=110$		MIN.	250	$V/\mu s$
$(dV/dt)_c$	$(dI/dt)_c=0.44A/ms$, $T_j=110$		MIN.	6	$V/\mu s$
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$		TYP.	3	μs
t_{off}	$T_j=25$			30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.4A$ $t_p=380\mu s$	$T_j=25$	1.45	V
V_{TO}	Threshold voltage	$T_j=125$	0.96	V
R_D	Dynamic resistance	$T_j=125$	225	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.2	mA

THERMAL RESISTANCES

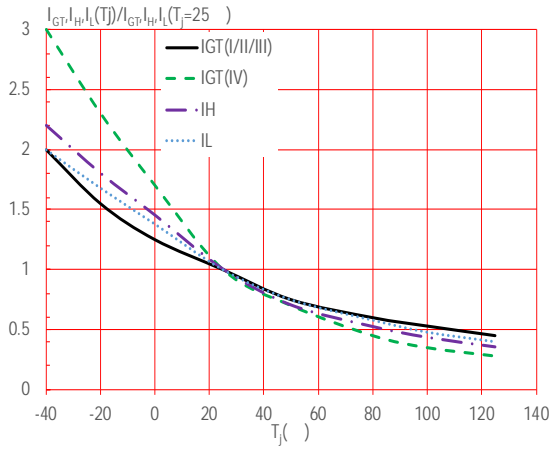
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	50	$/W$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=5cm^2$)	100	$/W$

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)
------------	----------------------------------

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.
Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.